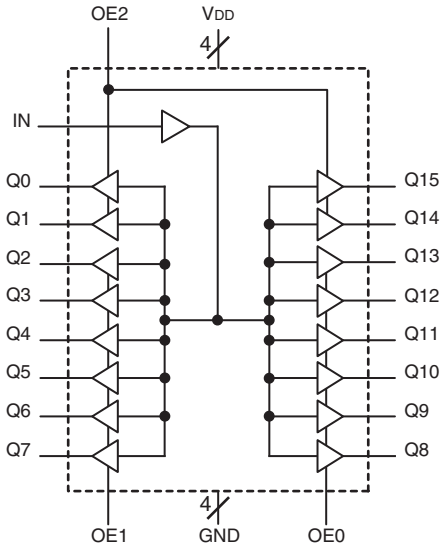
General Description

The 83115I is a low skew, 1-to-16 LVCMOS/ LVTTL Fanout Buffer. The 83115I single-ended clock input accepts LVCMOS or LVTTL input levels. The 83115I operates at full 3.3V supply mode over the industrial temperature range. Guaranteed output and part-to-part skew characteristics make the 83115I ideal for those clock distribution applications demanding well defined performance and repeatability.

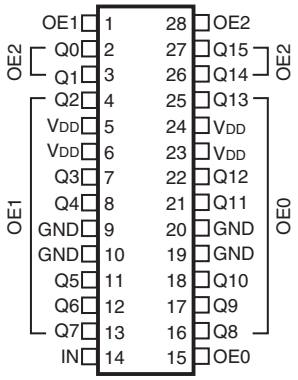
Features

- Sixteen LVCMOS / LVTTL outputs, 15Ω output impedance
- One LVCMOS / LVTTL clock input
- Maximum output frequency: 200MHz
- All inputs are 5V tolerant
- Output skew: 250ps (maximum)
- Part-to-part skew: 800ps (maximum)
- Additive phase jitter, RMS: 0.20ps (typical)
- Full 3.3V operating supply
- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) package

Block Diagram



Pin Assignment



83115I

28-Lead SSOP, 150mil
9.9mm x 3.9mm x 1.5mm package body
R Package
Top View

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Table 1. Pin Descriptions

Number	Name	Type		Description
1	OE1	Input	Pullup	Output enable pin. When LOW, forces outputs Q[2:7] to Hi-Z state. 5V tolerant. LVCMOS/LVTTL interface levels. See Table 3.
2, 3, 4, 7, 8, 11, 12, 13, 16, 17, 18, 21, 22, 25, 26, 27	Q0, Q1, Q2, Q3, Q4, Q5, Q6, Q7, Q8, Q9, Q10, Q11, Q12, Q13, Q14, Q15	Output		Single-ended clock outputs. 15Ω output impedance. LVCMOS/LVTTL interface levels.
5, 6, 23, 24	V_{DD}	Power		Positive supply pins.
9, 10, 19, 20	GND	Power		Power supply ground.
14	IN	Input	Pulldown	Single-ended clock input. 5V tolerant. LVCMOS/LVTTL interface levels.
15	OE0	Input	Pullup	Output enable pin. When LOW, forces outputs Q[8:13] to Hi-Z state. 5V tolerant. LVCMOS/LVTTL interface levels. See Table 3.
28	OE2	Input	Pullup	Output enable pin. When LOW, forces outputs Q[0:1] and Q[14:15] to Hi-Z state. 5V tolerant. LVCMOS/LVTTL interface levels. See Table 3.

NOTE: *Pullup and Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics,* for typical values.

Table 2. Pin Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C_{IN}	Input Capacitance			4		pF
R_{PULLUP}	Input Pullup Resistor			51		kΩ
$R_{PULLDOWN}$	Input Pulldown Resistor			51		kΩ
C_{PD}	Power Dissipation Capacitance (per output); NOTE 1	V_{DD} = 3.465V		11		pF
R_{OUT}	Output Impedance	V_{DD} = 3.3V		15		Ω

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Function Tables

Table 3. OEx Function Table

Inputs			Outputs		
OE0	OE1	OE2	Control OE2 Q[0:1], Q[14:15]	Control OE1 Q[2:7]	Control OE0 Q[8:13]
0	0	0	Hi-Z	Hi-Z	Hi-Z
0	0	1	Active	Hi-Z	Hi-Z
0	1	0	Hi-Z	Active	Hi-Z
0	1	1	Active	Active	Hi-Z
1	0	0	Hi-Z	Hi-Z	Active
1	0	1	Active	Hi-Z	Active
1	1	0	Hi-Z	Active	Active
1	1	1	Active	Active	Active

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics or AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, V_{DD}	4.6V
Inputs, V_I	-0.5V to V_{DD} + 0.5V
Outputs, V_O	-0.5V to V_{DD} + 0.5V
Package Thermal Impedance, θ_{JA}	49°C/W (0 lfpm)
Storage Temperature, T_{STG}	-65°C to 150°C

DC Electrical Characteristics

Table 4A. Power Supply DC Characteristics, V_{DD} = 3.3V ± 5%, T_A = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Positive Supply Voltage		3.135	3.3	3.465	V
I_{DD}	Power Supply Current				50	mA

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Table 4B. LVCMOS/LVTTL DC Characteristics, V_{DD} = 3.3V ± 5%, T_A = -40°C to 85°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage	OE0:OE2		2		V_{DD} + 0.3	V
		IN		2		V_{DD} + 0.3	V
V_{IL}	Input Low Voltage	OE0:OE2		-0.3		0.8	V
		IN		-0.3		1.3	V
I_{IH}	Input High Current	OE0:OE2	V_{DD} = V_{IN} = 3.465V			5	µA
		IN	V_{DD} = V_{IN} = 3.465V			150	µA
I_{IL}	Input Low Current	OE0:OE2	V_{DD} = 3.465V, V_{IN} = 0V	-150			µA
		IN	V_{DD} = 3.465V, V_{IN} = 0V	-5			µA
V_{OH}	Output High Voltage; NOTE 1		V_{DD} = 3.3V ± 5%	2.6			V
V_{OL}	Output Low Voltage; NOTE 1		V_{DD} = 3.3V ± 5%			0.5	V
I_{OZL}	Output Hi-Z Current Low					5	µA
I_{OZH}	Output Hi-Z Current High					5	µA

NOTE 1: Outputs terminated with 50Ω to V_{DD}/2. See Parameter Measurement Information, *Output Load Test Circuit diagram.*

AC Electrical Characteristics

Table 5. AC Characteristics, V_{DD} = 3.3V ± 5%, T_A = -40°C to 85°C

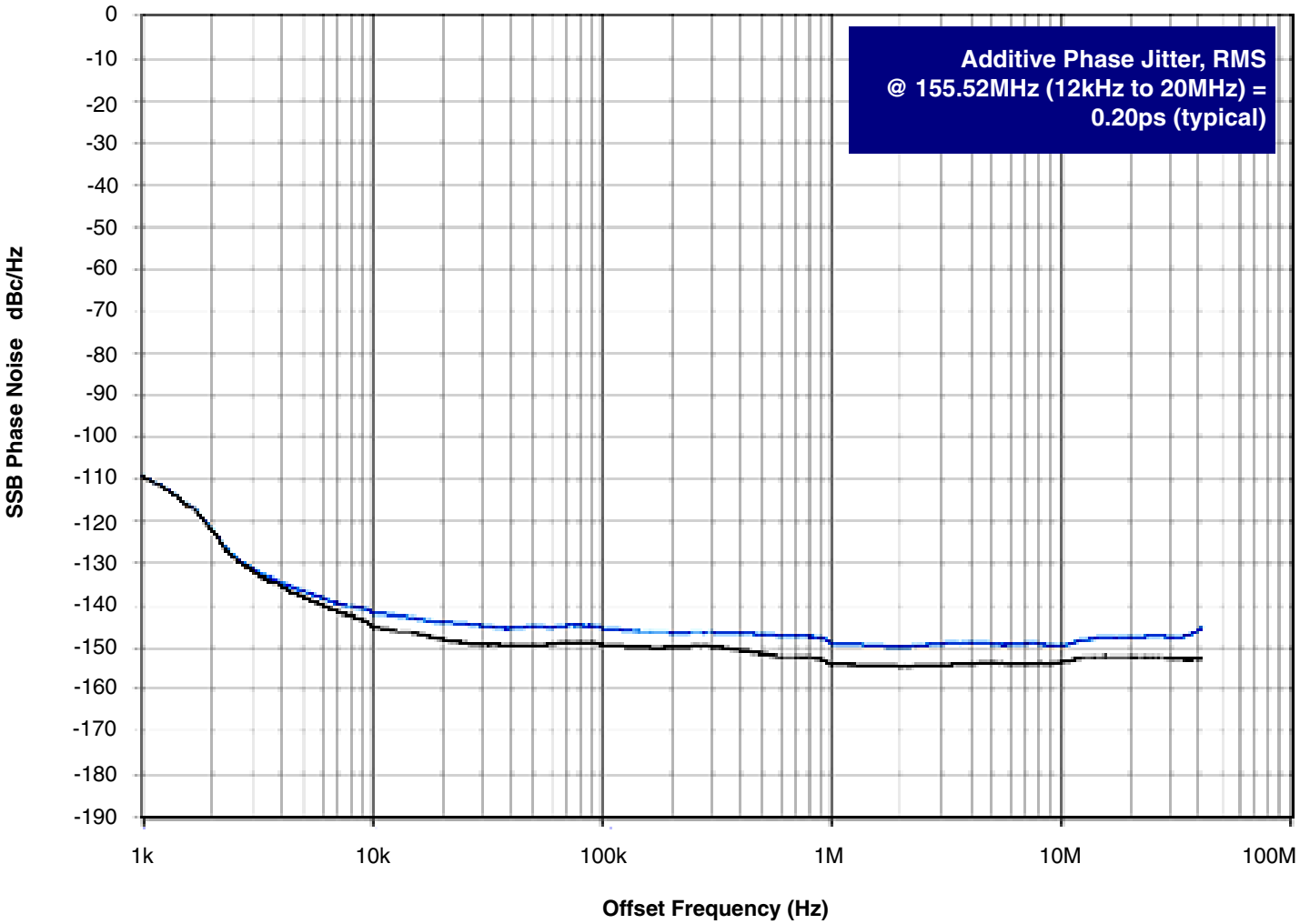
Parameter	Symbol	Test Conditions	Minimum	Typical	Maximum	Units
f_{MAX}	Output Frequency				200	MHz
	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section	Integration Range: 12kHz – 20MHz		0.20		ps
tp_{LH}	Propagation Delay; NOTE 1	$f \leq$ 200MHz	1.7	2.4	3.1	ns
*t*sk(o)	Output Skew; NOTE 2, 4	Measured on the Rising Edge @ V_{DD}/2		150	250	ps
*t*sk(pp)	Part-to-Part Skew; NOTE 3, 4	Measured on the Rising Edge @ V_{DD}/2			800	ps
t_R / t_F	Output Rise/Fall Time4	20% to 80%	400		800	ps
odc	Output Duty Cycle		45		55	%
t_{EN}	Output Enable Time				20	ns
t_{DIS}	Output Disable Time				20	ns

All parameters measured at f_{MAX} unless noted otherwise.
NOTE 1: Measured from V_{DD}/2 of the input to V_{DD}/2 of the output.
NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at V_{DD}/2.
NOTE 3: Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at V_{DD}/2.
NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.

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Additive Phase Jitter

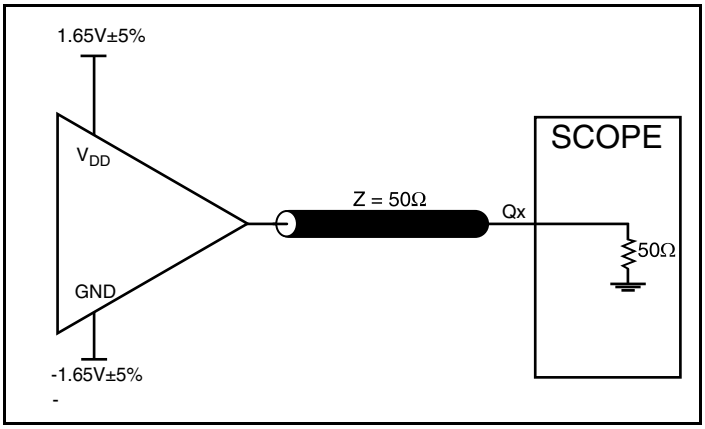
The spectral purity in a band at a specific offset from the fundamental compared to the power of the fundamental is called the ***dBc Phase Noise.*** This value is normally expressed using a Phase noise plot and is most often the specified plot in many applications. Phase noise is defined as the ratio of the noise power present in a 1Hz band at a specified offset from the fundamental frequency to the power value of the fundamental. This ratio is expressed in decibels (dBm) or a ratio of the power in the 1Hz band to the power in the fundamental. When the required offset is specified, the phase noise is called a ***dBc*** value, which simply means dBm at a specified offset from the fundamental. By investigating jitter in the frequency domain, we get a better understanding of its effects on the desired application over the entire time record of the signal. It is mathematically possible to calculate an expected bit error rate given a phase noise plot.



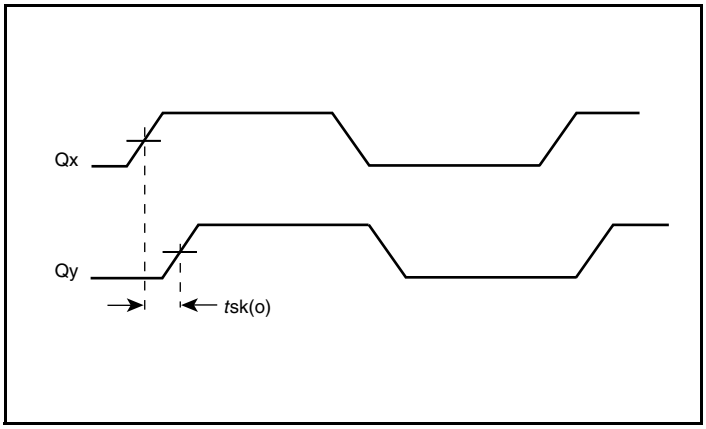
As with most timing specifications, phase noise measurements has issues relating to the limitations of the equipment. Often the noise floor of the equipment is higher than the noise floor of the device. This is illustrated above. The device meets the noise floor of what is shown, but can actually be lower. The phase noise is dependant on the input source and measurement equipment.

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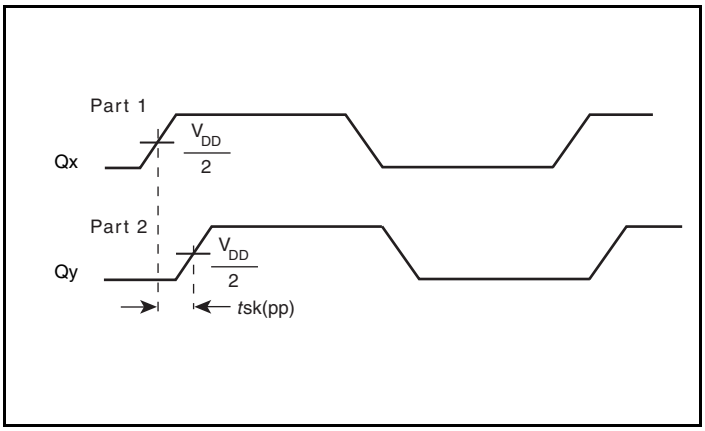
Parameter Measurement Information



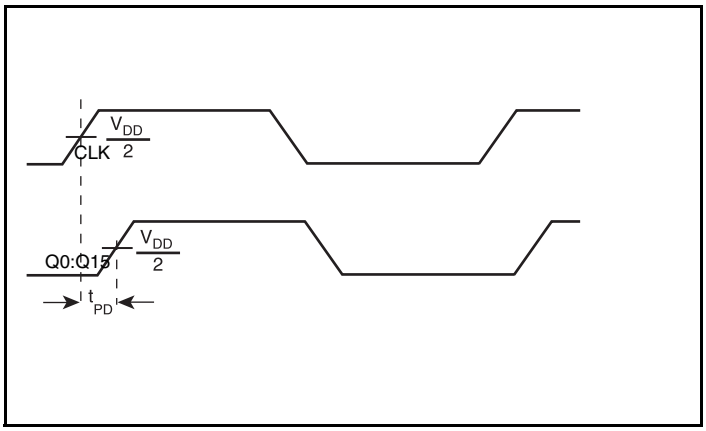
3.3V Output Load AC Test Circuit



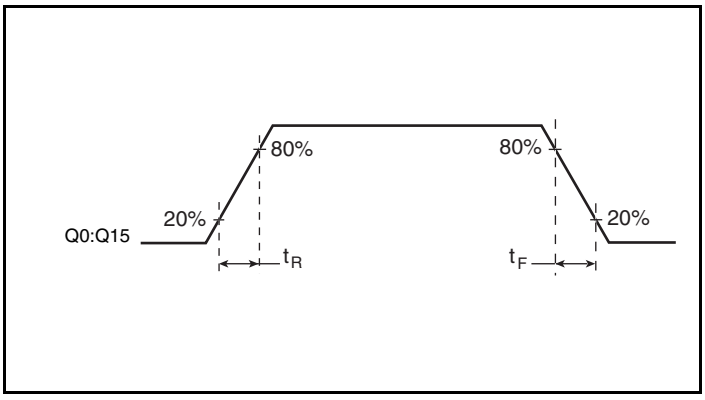
Output Skew



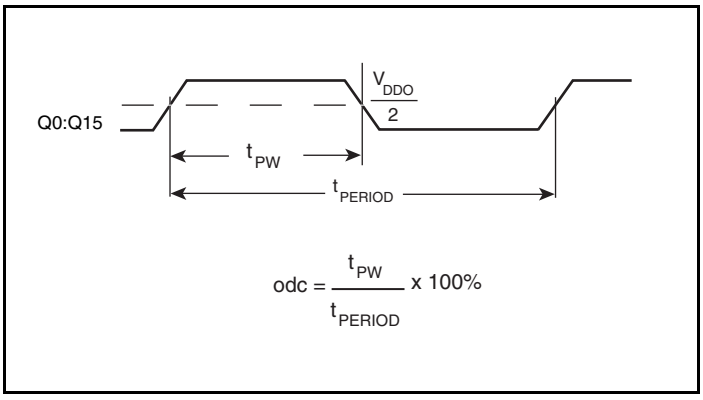
Part-to-Part Skew



Propagation Delay



Output Rise/Fall Time



Output Duty Cycle/Pulse Width/Period

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Application Information

Recommendations for Unused Input and Output Pins

Inputs:

LVCMOS Control Pins

All control pins have internal pull-ups or pull-downs; additional resistance is not required but can be added for additional protection. A 1kΩ resistor can be used.

Outputs:

LVCMOS Outputs

All unused LVCMOS output can be left floating. There should be no trace attached.

Reliability Information

Table 6. θ_{JA} vs. Air Flow Table for a 28 Lead SSOP, 150MIL

θ_{JA} vs. Air Flow			
Linear Feet per Minute	**0**	**200**	**500**
Multi-Layer PCB, JEDEC Standard Test Boards	49°C/W	36°C/W	30°C/W

Transistor Count

The transistor count for 83115I: 985

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Package Outline and Package Dimension

Package Outline - G Suffix for 28 Lead SSOP

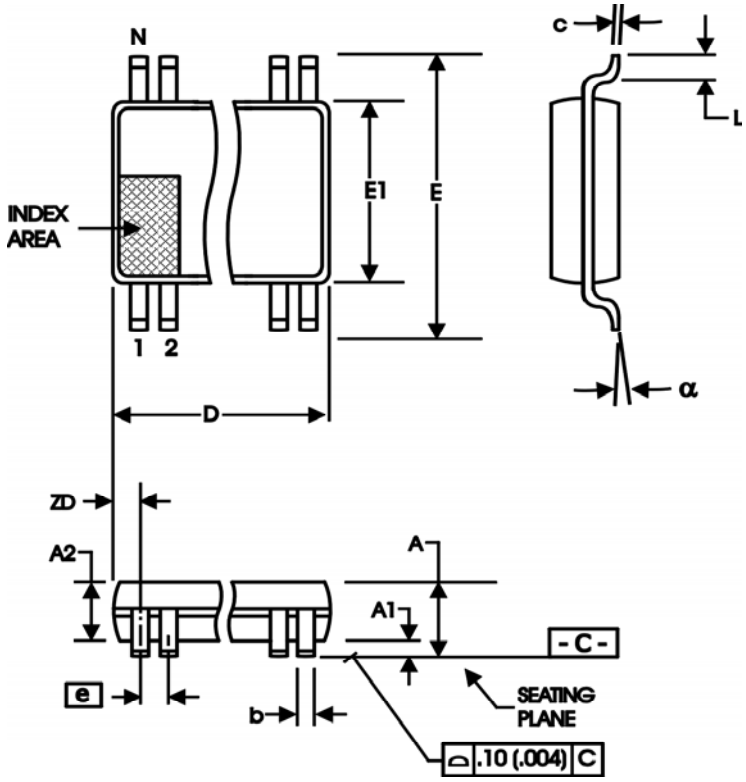


Table 7. Package Dimensions for 28 Lead SSOP

All Dimensions in Millimeters		
Symbol	**Minimum**	**Maximum**
N	28	
A	1.35	1.75
A1	0.10	0.25
A2		1.50
b	0.20	0.30
c	0.18	0.25
D	9.80	10.00
E	5.80	6.20
E1	3.80	4.00
e	0.635 Basic	
L	0.40	1.27
α	0°	8°
ZD	0.84 Ref	

Reference Document: JEDEC Publication 95, MO-137

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Ordering Information

Table 8. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
83115BRILF	83115BRILF	“Lead-Free” 28 Lead SSOP	Tube	-40°C to 85°C
83115BRILFT	83115BRILF	“Lead-Free” 28 Lead SSOP	Tape & Reel	-40°C to 85°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

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Revision History Sheet

Rev	Table	Page	Description of Change	Date
B	T5	4	AC Characteristics Table - changed Output Rise/Fall Time limits from 650ps min./1150ps max. to 400ps min./800ps max.	3/19/08
B	T8	9	Ordering Information - removed leaded devices. Updated data sheet format.	4/28/15

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(Rev.1.0 Mar 2020)

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